

Features

- Extremely Low Saturation Voltage
- Halogen Free. "Green" Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings @ 25°C Unless Otherwise Specified

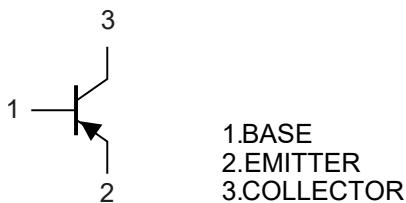
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 357°C/W Junction to Ambient

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-1.5	A
Continuous Base Current	I_B	-0.5	A
Power Dissipation	P_D	350	mW

Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

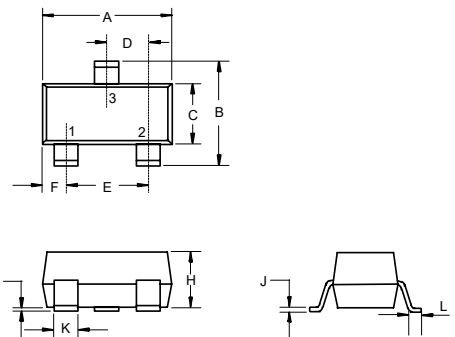
Marking: 718

Internal Structure



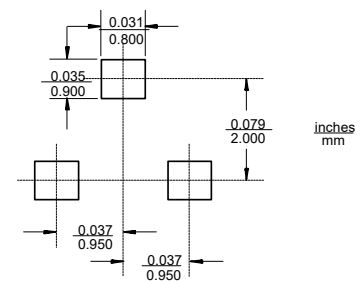
PNP Silicon Planar High Performance Transistor

SOT-23



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

Suggested Solder Pad Layout



Electrical Characteristics @ $T_A=25^\circ\text{C}$ Unless Otherwise Specified

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage*	$V_{(BR)CBO}$	-20			V	$I_C=-100\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-20			V	$I_C=-10\text{mA}, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-7			V	$I_E=-100\mu\text{A}, I_C=0$
Collector-Base Cutoff Current	I_{CBO}			-100	nA	$V_{CB}=-15\text{V}, I_E=0$
Emitter-Base Cutoff Current	I_{EBO}			-100	nA	$V_{EB}=-4\text{V}, I_C=0$
DC Current Gain*	$h_{FE(1)}$	300				$V_{CE}=-2\text{V}, I_C=-10\text{mA}$
	$h_{FE(2)}$	300				$V_{CE}=-2\text{V}, I_C=-100\text{mA}$
	$h_{FE(3)}$	150				$V_{CE}=-2\text{V}, I_C=-2\text{A}$
	$h_{FE(4)}$	35				$V_{CE}=-2\text{V}, I_C=-4\text{A}$
Collector-Emitter Saturation Voltage*	$V_{CE(sat)}$			-0.04	V	$I_C=-100\text{mA}, I_B=-10\text{mA}$
				-0.20	V	$I_C=-1\text{A}, I_B=-20\text{mA}$
				-0.22	V	$I_C=-1.5\text{A}, I_B=-50\text{mA}$
Base-Emitter Saturation Voltage*	$V_{BE(sat)}$			-1.0	V	$I_C=-1.5\text{A}, I_B=-50\text{mA}$
Base-Emitter Voltage*	V_{BE}			-1.0	V	$V_{CE}=-2\text{V}, I_C=-2\text{A}$
Transition Frequency	f_T	150			MHz	$V_{CE}=-10\text{V}, I_C=-50\text{mA}, f=100\text{MHz}$
Turn-on Time	$t_{(on)}$		40		ns	$V_{CC}=-10\text{V}, I_C=-1\text{A}, I_{B1}=I_{B2}=-20\text{mA}$
Turn-off Time	$t_{(off)}$		670		ns	
Collector-Base Capacitance	C_{ob}			30	pF	$V_{CB}=-10\text{V}, f=1\text{MHz}$

*.Pulse test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Curve Characteristics

Fig. 1 - Static Characteristics

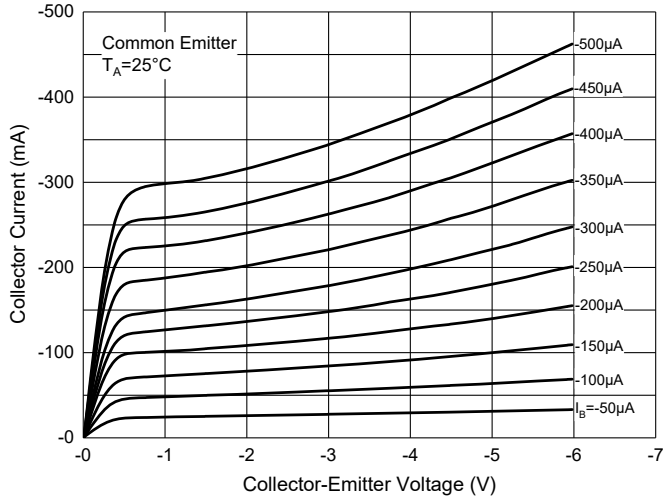


Fig. 2 - DC Current Gain Characteristics

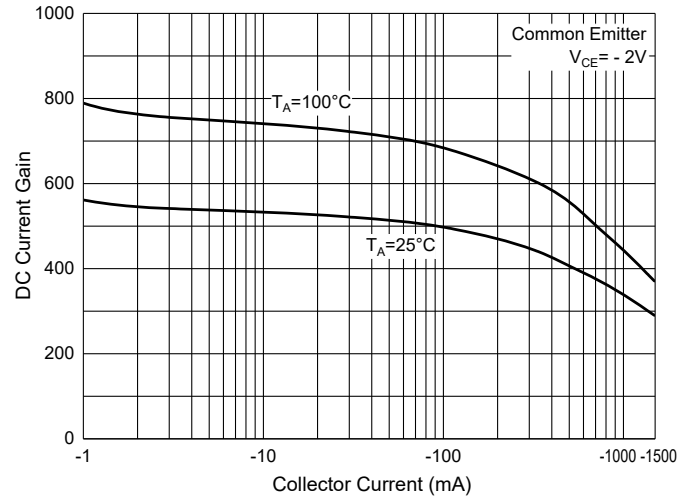


Fig. 3 - Base-Emitter Saturation Voltage Characteristics

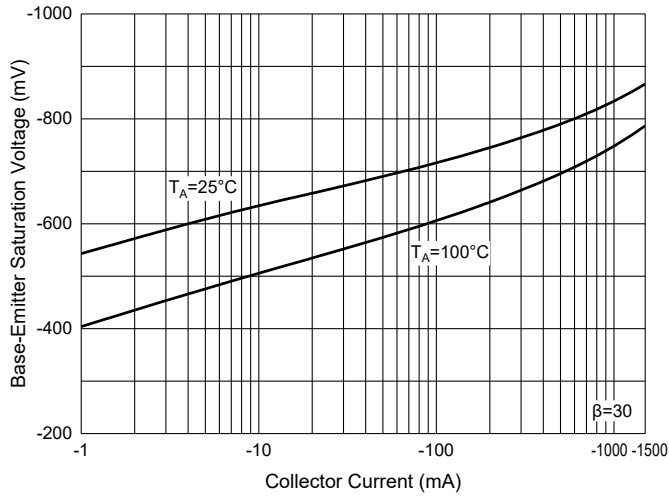


Fig. 4 - Collector-Emitter Saturation Voltage Characteristics

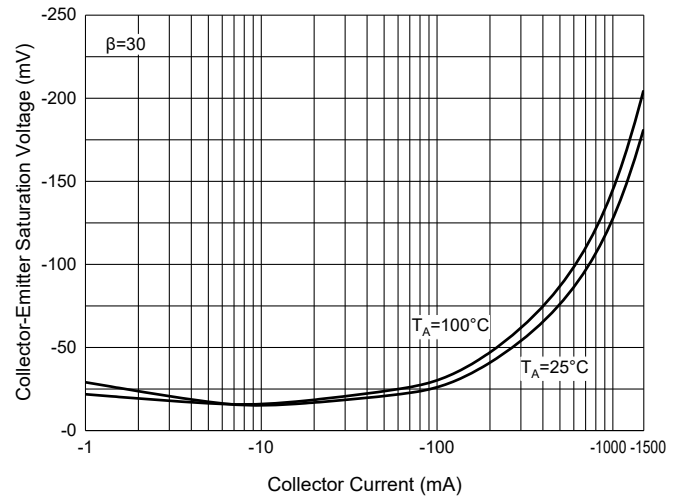


Fig. 5 - Base-Emitter Voltage Characteristics

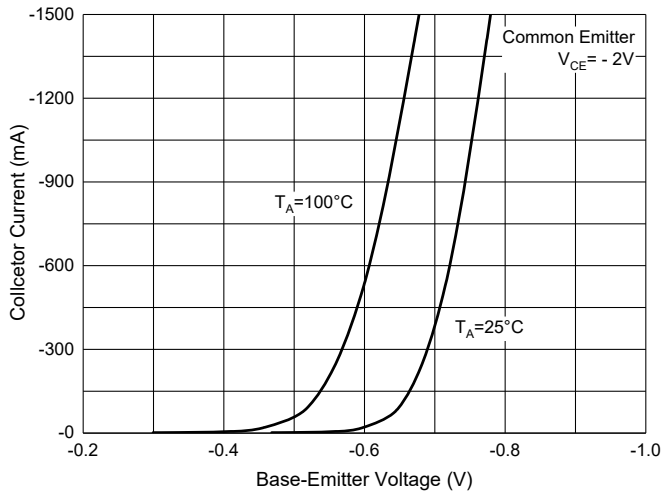


Fig. 6 - Collector Power Derating Curve

